

Cheol-Joo Kim

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

40
papers

3,409
citations

19
h-index

46
g-index

46
ext. papers

3,890
ext. citations

13.7
avg, IF

5.04
L-index

#	Paper	IF	Citations
40	Substrate-Dependent Growth Mode Control of MoS ₂ Monolayers: Implications for Hydrogen Evolution and Field-Effect Transistors. <i>ACS Applied Nano Materials</i> , 2022 , 5, 4336-4342	5.6	0
39	Direct Synthesis of Molybdenum Phosphide Nanorods on Silicon Using Graphene at the Heterointerface for Efficient Photoelectrochemical Water Reduction. <i>Nano-Micro Letters</i> , 2021 , 13, 81	19.5	6
38	Pristine Graphene Insertion at the Metal/Semiconductor Interface to Minimize Metal-Induced Gap States. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 22828-22835	9.5	1
37	Graphene Nanoribbon Grids of Sub-10 nm Widths with High Electrical Connectivity. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 28593-28599	9.5	2
36	Atomically Smooth Graphene-Based Hybrid Template for the Epitaxial Growth of Organic Semiconductor Crystals. <i>Advanced Functional Materials</i> , 2021 , 31, 2008813	15.6	3
35	Nanoscale Molecular Building Blocks for Layer-by-Layer Assembly. <i>Advanced Materials Interfaces</i> , 2020 , 7, 2000522	4.6	3
34	Metal Nanoparticle Exsolution on a Perovskite Stannate Support with High Electrical Conductivity. <i>Nano Letters</i> , 2020 , 20, 3538-3544	11.5	9
33	All-Dry Transfer of Graphene Film by van der Waals Interactions. <i>Nano Letters</i> , 2019 , 19, 3590-3596	11.5	18
32	Stacking angle-tunable photoluminescence from interlayer exciton states in twisted bilayer graphene. <i>Nature Communications</i> , 2019 , 10, 1445	17.4	42
31	Klein tunnelling and electron trapping in nanometre-scale graphene quantum dots. <i>Nature Physics</i> , 2016 , 12, 1069-1075	16.2	103
30	Atomically Thin Ohmic Edge Contacts Between Two-Dimensional Materials. <i>ACS Nano</i> , 2016 , 10, 6392-9	16.7	144
29	Chiral atomically thin films. <i>Nature Nanotechnology</i> , 2016 , 11, 520-524	28.7	117
28	Imaging chiral symmetry breaking from Kekulé bond order in graphene. <i>Nature Physics</i> , 2016 , 12, 950-958	16.2	56
27	High-mobility three-atom-thick semiconducting films with wafer-scale homogeneity. <i>Nature</i> , 2015 , 520, 656-60	50.4	1224
26	Polycrystalline graphene with single crystalline electronic structure. <i>Nano Letters</i> , 2014 , 14, 5706-11	11.5	112
25	Stacking order dependent second harmonic generation and topological defects in h-BN bilayers. <i>Nano Letters</i> , 2013 , 13, 5660-5	11.5	106
24	Hyperspectral imaging of structure and composition in atomically thin heterostructures. <i>Nano Letters</i> , 2013 , 13, 3942-6	11.5	37

23	Spatially resolved photodetection in leaky ferroelectric BiFeO ₃ . <i>Advanced Materials</i> , 2012 , 24, OP49-53	24	25
22	Photodetection: Spatially Resolved Photodetection in Leaky Ferroelectric BiFeO ₃ (Adv. Mater. 10/2012). <i>Advanced Materials</i> , 2012 , 24, OP48-OP48	24	
21	Vectorial nanowire growth by local kinetic manipulation. <i>Journal of Crystal Growth</i> , 2012 , 345, 56-60	1.6	2
20	Graphene and boron nitride lateral heterostructures for atomically thin circuitry. <i>Nature</i> , 2012 , 488, 627-324	3.4	650
19	Large electroabsorption susceptibility mediated by internal photoconductive gain in Ge nanowires. <i>Nano Letters</i> , 2012 , 12, 5913-8	11.5	6
18	Depolarization effect in optical absorption measurements of one- and two-dimensional nanostructures. <i>Applied Physics Letters</i> , 2012 , 101, 123102	3.4	10
17	Determination of the photocarrier diffusion length in intrinsic Ge nanowires. <i>Optics Express</i> , 2011 , 19, 6119-24	3.3	8
16	On-nanowire band-graded Si:Ge photodetectors. <i>Advanced Materials</i> , 2011 , 23, 1025-9	24	33
15	Diameter-dependent internal gain in ohmic Ge nanowire photodetectors. <i>Nano Letters</i> , 2010 , 10, 2043-8	11.5	137
14	Vertically aligned Si intranowire p-n diodes by large-area epitaxial growth. <i>Applied Physics Letters</i> , 2009 , 94, 173105	3.4	13
13	Unconventional roles of metal catalysts in chemical-vapor syntheses of single-crystalline nanowires. <i>Journal of Applied Physics</i> , 2009 , 105, 122407	2.5	15
12	Directionally Integrated VLS Nanowire Growth in a Local Temperature Gradient. <i>Angewandte Chemie</i> , 2009 , 121, 7502-7506	3.6	2
11	Directionally integrated VLS nanowire growth in a local temperature gradient. <i>Angewandte Chemie - International Edition</i> , 2009 , 48, 7366-70	16.4	17
10	Electrical detection of VEGFs for cancer diagnoses using anti-vascular endothelial growth factor aptamer-modified Si nanowire FETs. <i>Biosensors and Bioelectronics</i> , 2009 , 24, 1801-5	11.8	122
9	Massive integration of inorganic nanowire-based structures on solid substrates for device applications. <i>Journal of Materials Chemistry</i> , 2009 , 19, 901		14
8	Si-type Si-nanowire-based Field-effect Transistors for Electric Detection of a Biomarker: Matrix Metalloproteinase-9. <i>Journal of the Korean Physical Society</i> , 2009 , 55, 232-235	0.6	8
7	Thermodynamic analysis for the size-dependence of nanowire composition grown by a vapor-liquid-solid method. <i>Calphad: Computer Coupling of Phase Diagrams and Thermochemistry</i> , 2008 , 32, 669-674	1.9	13
6	The role of NiO _x overlayers on spontaneous growth of NiSi ₃ nanowires from Ni seed layers. <i>Nano Letters</i> , 2008 , 8, 431-6	11.5	50

5	Axially graded heteroepitaxy and Raman spectroscopic characterizations of Si _{1-x} Ge _x nanowires. <i>Applied Physics Letters</i> , 2008 , 92, 263111	3.4	12
4	Low-Temperature Deterministic Growth of Ge Nanowires Using Cu Solid Catalysts. <i>Advanced Materials</i> , 2008 , 20, 4684-4690	24	68
3	Spontaneous Chemical Vapor Growth of NiSi Nanowires and Their Metallic Properties. <i>Advanced Materials</i> , 2007 , 19, 3637-3642	24	93
2	Fabrication of Si _{1-x} Ge _x alloy nanowire field-effect transistors. <i>Applied Physics Letters</i> , 2007 , 91, 033104	3.4	29
1	Band-gap modulation in single-crystalline Si _{1-x} Ge _x nanowires. <i>Nano Letters</i> , 2006 , 6, 2679-84	11.5	99